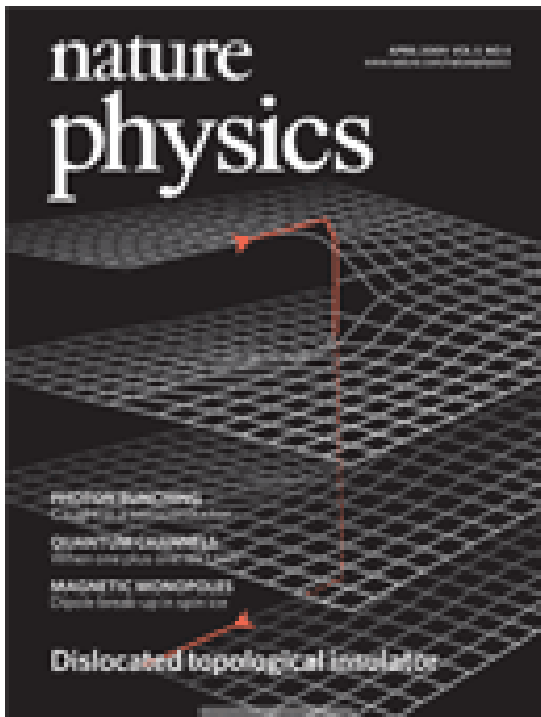


# Metallic Topological Defects inside a Topological Band Insulator

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**Yi Zhang**

*Ref:* Nature Physics 5, 289 (2009).  
[arXiv:0810.5121](https://arxiv.org/abs/0810.5121)

## What is topological band insulator?

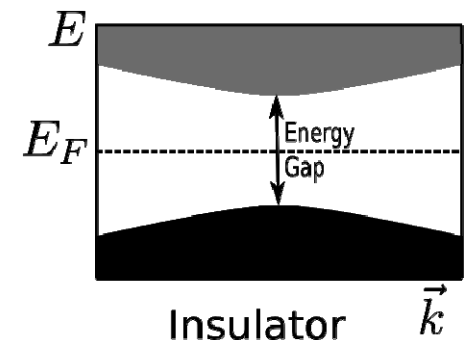
- Topology characterizes the identity of objects up to deformation, e.g. genus of surfaces



Figure courtesy C. Kane

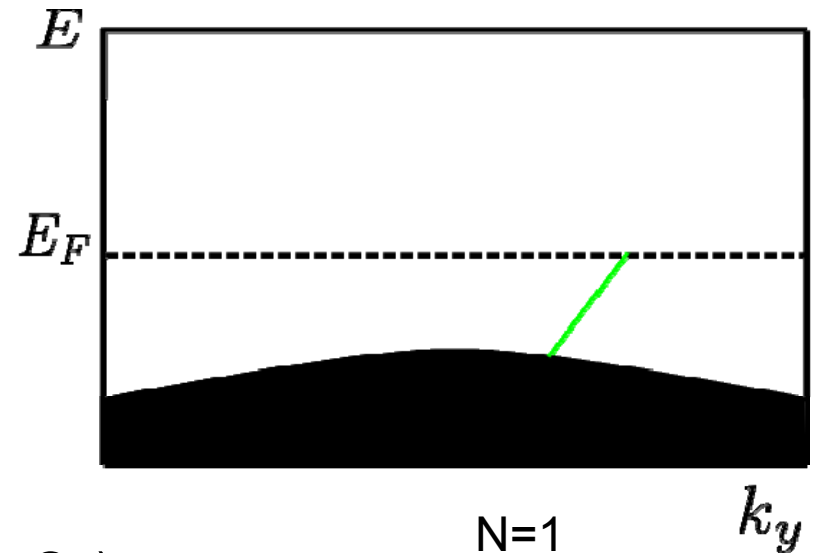
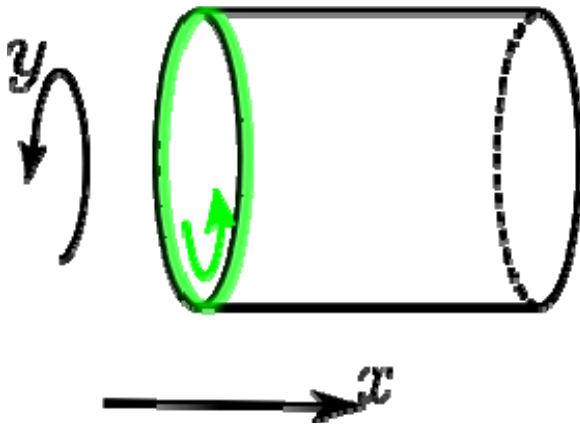
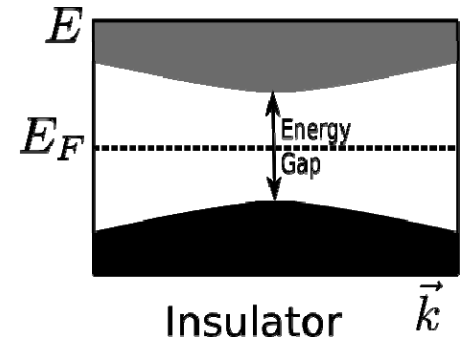
- Similarly, band insulator can be classified up to the deformation of band structure. Modify  $H$  smoothly preserving gap.

Simplest example- quantum hall insulator.



# Exotic Band Topology

- Integer Quantum Hall States:
  - Gapped in the bulk
  - Gapless Edge states that are **chiral**
    - (propagate in one direction only)
  - Leads to Quantized Hall effect



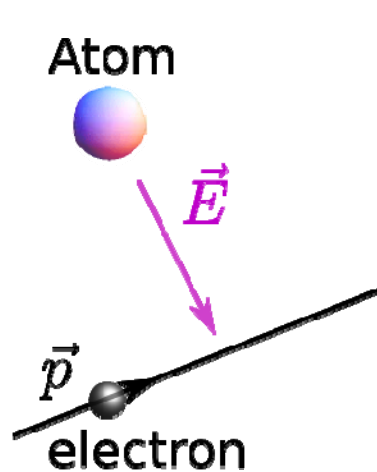
Also, superconducting analogs (p+ip Sc)

**Unconventional Surface/Edge states.**

“The edge is the window into the bulk” – X.G. Wen

# Can one realize a quantum hall like insulator WITHOUT a magnetic field?

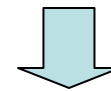
- **Yes:** Kane and Mele; Bernevig & Zhang (2005),
  - Spin-orbit interaction » spin-dependent magnetic field



$$H_{SO} = -\vec{\mu}_{spin} \cdot \left( -\frac{\vec{v} \times \vec{E}}{c^2} \right) \propto \vec{S} \cdot \vec{L}$$

Spin-orbit interaction is Time Reversal symmetric:

$$\vec{B} \text{ for } \uparrow, -\vec{B} \text{ for } \downarrow.$$



“Spin-Hall Effect”

# Topological insulator with spin-orbit interaction in $D=2$

- in 2D, with spin-orbit interaction, **time-reversal symmetric** topological insulator is labeled by a  $Z_2$  number  $\nu$ ,

$\nu=0$ : trivial;



C. Kane

$\nu=1$ : non-trivial



New phase of matter! (necessarily separated from trivial case by phase transition)



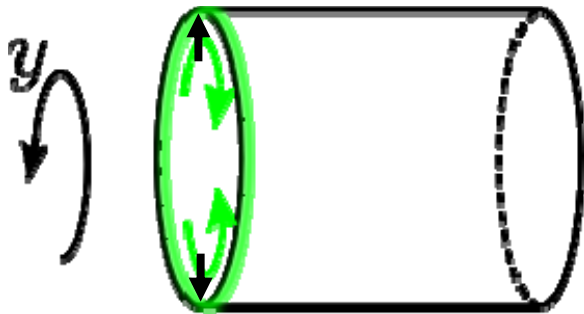
E. J. Mele

Quantum Spin Hall Insulator  
or  
2D topological Insulator

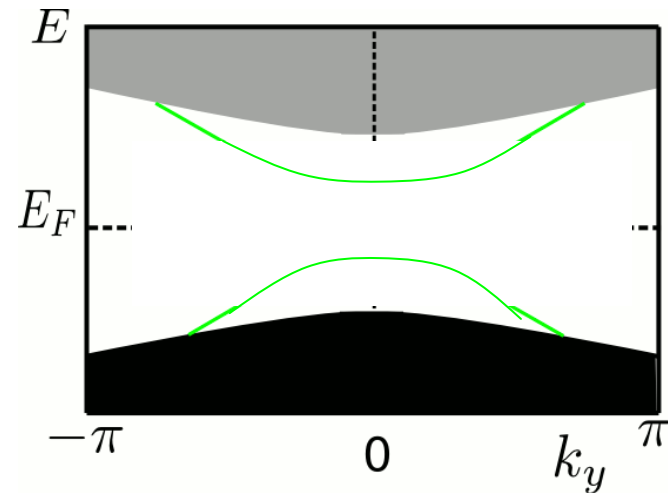
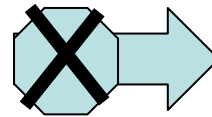
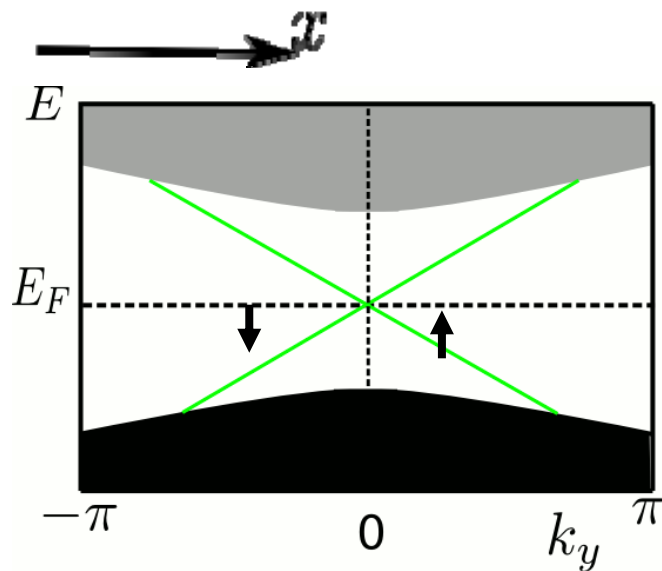
What are the edge states?

# Edge states of TR symmetric $Z_2$ T-I

Time reversal symmetry => two counter-propagating edge modes



Protected by Time Reversal,  
even if spin is not conserved.  
Only  $Z_2$  (even-odd) distinction.

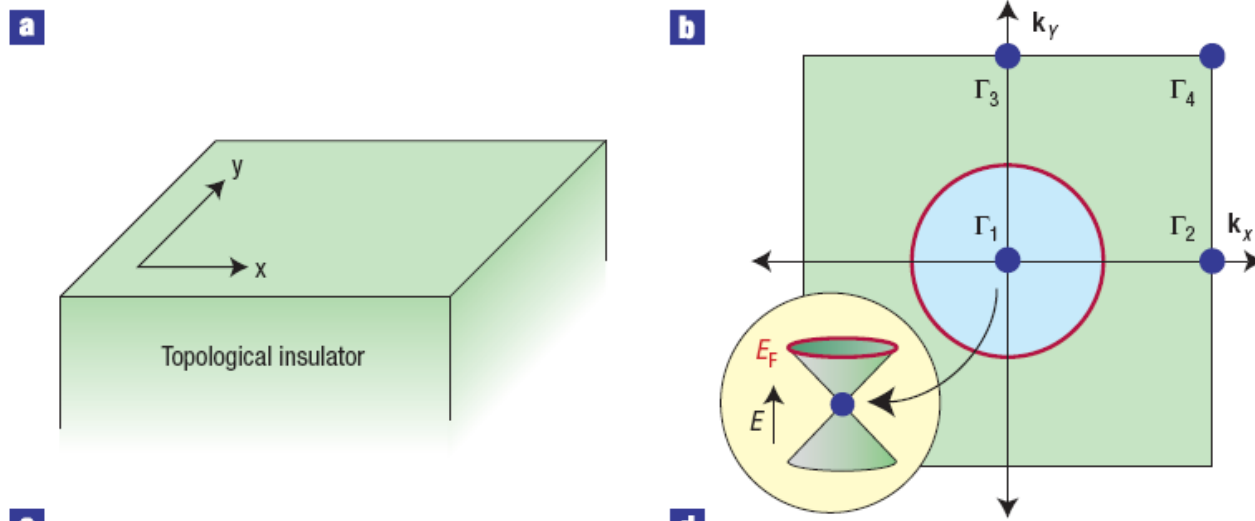


- Experimentally observed by transport measurements on HgTe quantum well (Bernevig et al., Science 2006; Konig et al. Science 2007)

# Topological insulator with spin-orbit interaction in $D=3$

- One obvious route to topological insulator in  $D=3$  :
  - Stack 2D layers of quantum spin Hall insulators.
  - Defined by the reciprocal vector of the stacking layers.  $\mathbf{G}_v$
  - ‘weak’ topological insulators.
- Less obvious possibility (no quantum Hall analog)
  - ‘strong’ topological insulators in  $D=3$ .
  - Characteristic feature – Surface state: single Dirac node.

Fu, Kane & Mele (2006), Moore & Balents (2006), Roy (2006).



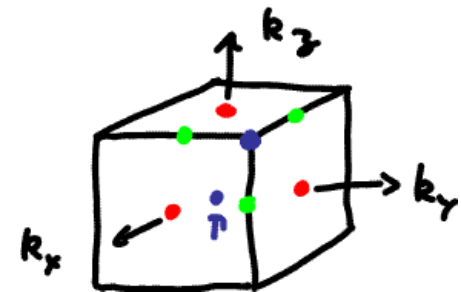
# Topological Indices in 3D

- Given a band structure, it is possible to calculate the following topological indices:

**Strong index  $\nu_0 \in (0,1)$ :**

*Physical Interpretation:*  $\nu_0=1 \Rightarrow$  Odd number of surface Dirac nodes

**'Weak' or Lattice indices:**  $\mathbf{M}_\nu$   
 time rev. invariant wave-vector  $\mathbf{M}_\nu = \frac{1}{2} \mathbf{G}_\nu$



*Physical Interpretation:*

$$\mathbf{M}_\nu = (\nu_1 \mathbf{G}_1 + \nu_2 \mathbf{G}_2 + \nu_3 \mathbf{G}_3) / 2$$

For Strong Insulator:

Location of Dirac node on Surface B.Zone (project  $\mathbf{M}_\nu$  on surface)

For Weak insulator:

Stacking of 2D quantum spin Hall layers  $\mathbf{M}_\nu = \mathbf{G}_\nu / 2$

OR Location of one of the pair of Dirac nodes on surface (other at  $\Gamma$ )

$\nu_0 = 0$  AND  $\mathbf{M}_\nu = 0$  : then trivial insulator

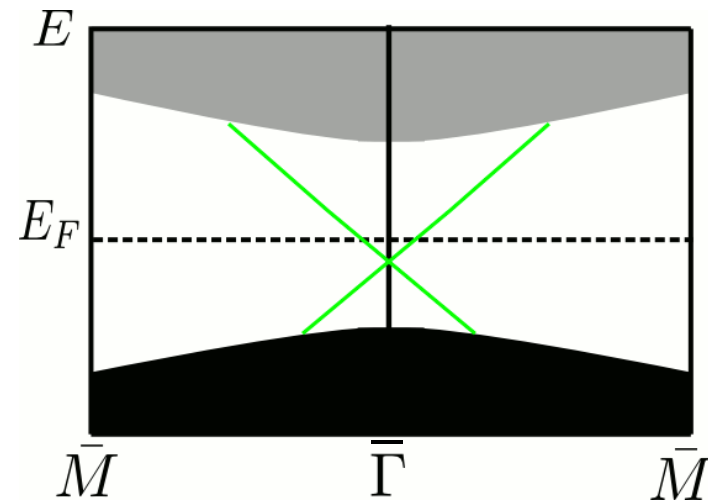
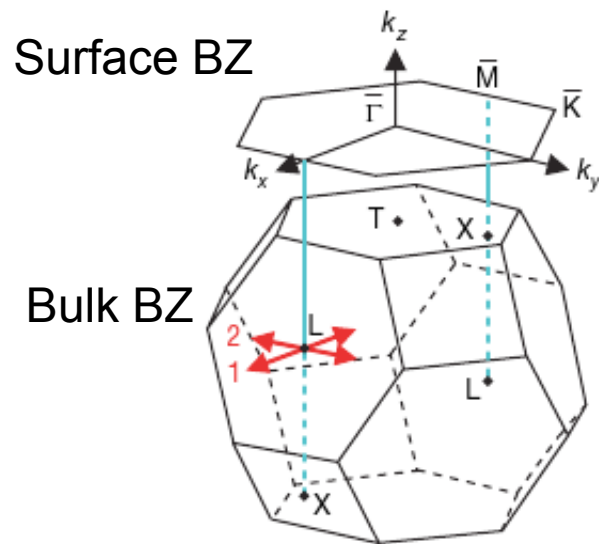
# 3D Strong T-I is found in experiments

- $\text{Bi}_{1-x}\text{Sb}_x$

Theory: L. Fu & C. L. Kane (07)

- **ARPES** (Angle Resolved Photoemission Spectroscopy)

Directly measures surface electron dispersion.



Signature: Odd # of FS crossings from  $\bar{\Gamma}$  to  $\bar{M}$

# 3D Strong T-I is found in experiments

- $\text{Bi}_{1-x}\text{Sb}_x$

Theory: L. Fu & C. L. Kane (07)

Surface modes ARPES  
confirms strong T-I.

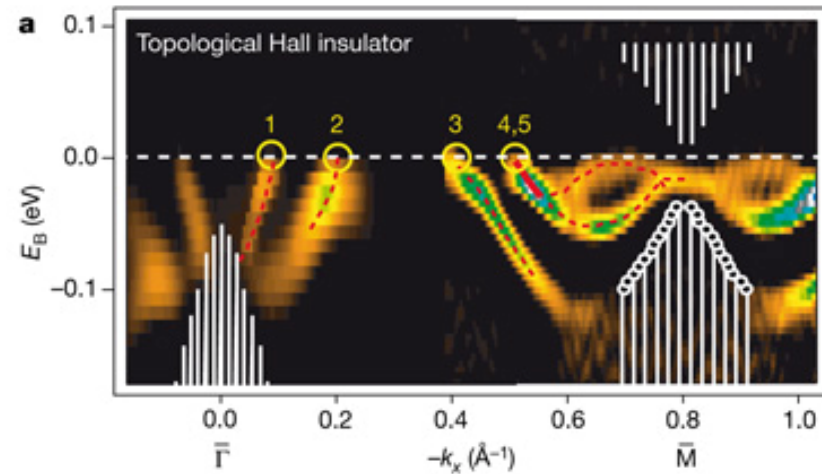
Experiment: D. Hsieh, D. Qian, L. Wray,  
Y. Xia, Y. S. Hor, R. J. Cava and M. Z.  
Hasan, Nature (08)

$$\nu_0 = 1; \mathbf{M}_\nu \propto (111)$$

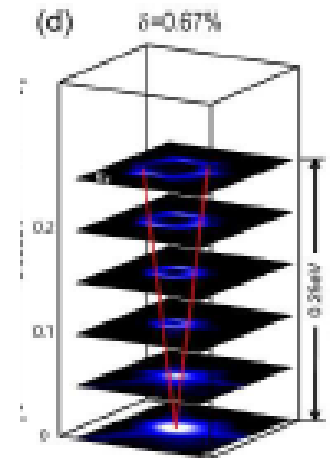
- New materials:  $\text{Bi}_2\text{Se}_3$ ,  $\text{Bi}_2\text{Te}_3$

– Eg. Y. Chen et al. (2009).

$$\nu_0 = 1; \mathbf{M}_\nu = 0$$



5-crossings

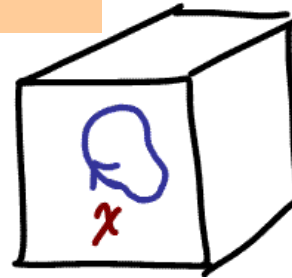


# Broken Symmetry + Exotic Band Topology

- Superconducting order parameter:  $|\Psi_0|e^{i\varphi}$
- Vortex defects:  $\oint \nabla \varphi \cdot dr = 2\pi m$



$p_x + ip_y$   
Vortex  
Majorana  
Mode



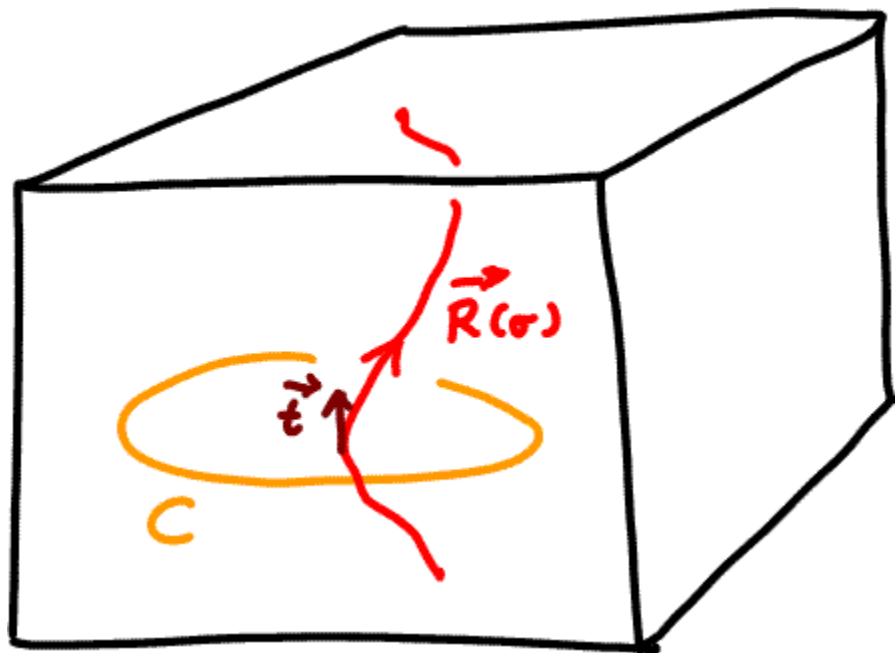
He<sub>3</sub>-B phase  
Propagating  
Majorana modes  
on vortex line

- Crystalline Solid – also broken symmetry phase.
  - Analog in topological insulators? **YES**
    - Dislocations host counter-propagating 1D modes. Like the edge of 2D QSH Insulator - Helical Metal.
    - Protected against disorder scattering – ideal quantum wire inside a bulk solid.

# Line Defects in a Crystal

- Dislocations:

Defined by location  $\mathbf{R}(\sigma)$  and 'strength'  $\mathbf{B}$ .



$$\vec{r}_n = \vec{r}_n^{(0)} + \vec{u}(r_n)$$

$\uparrow$  atom locations       $\uparrow$  perfect crystal       $\uparrow$  order parameter NOT single valued.

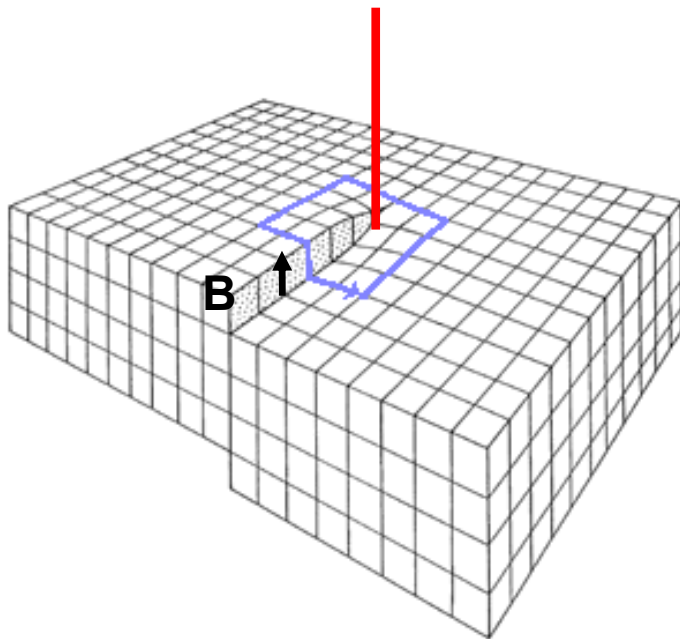
$$\oint_C d\vec{l} \cdot \vec{\nabla} \vec{u} = \vec{B} \quad \{\alpha \text{ lattice vector}\}$$

**B – Burgers Vector**, must stay constant along the length and is quantized to lattice vectors. (Like vorticity)

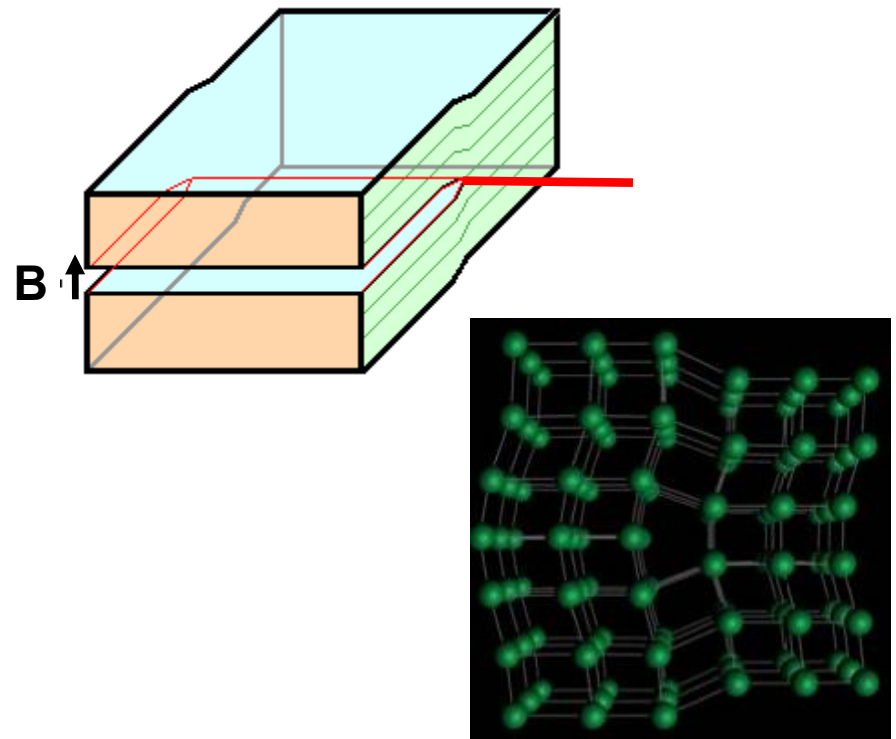
# Visualizing Dislocations

- Volterra Process:
  - Cut with an imaginary plane, that ends on the dislocation line  $\mathbf{R}(\sigma)$
  - Move all atoms on one side of the plane by the Burgers vector  $\mathbf{B}$
  - Add/remove atoms if required.

SCREW DISLOCATION:  $\mathbf{t} \parallel \mathbf{B}$

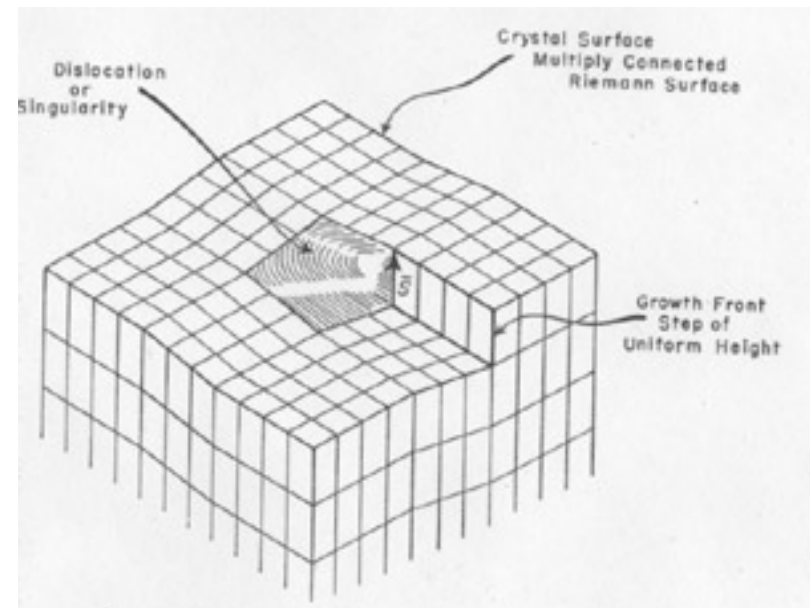
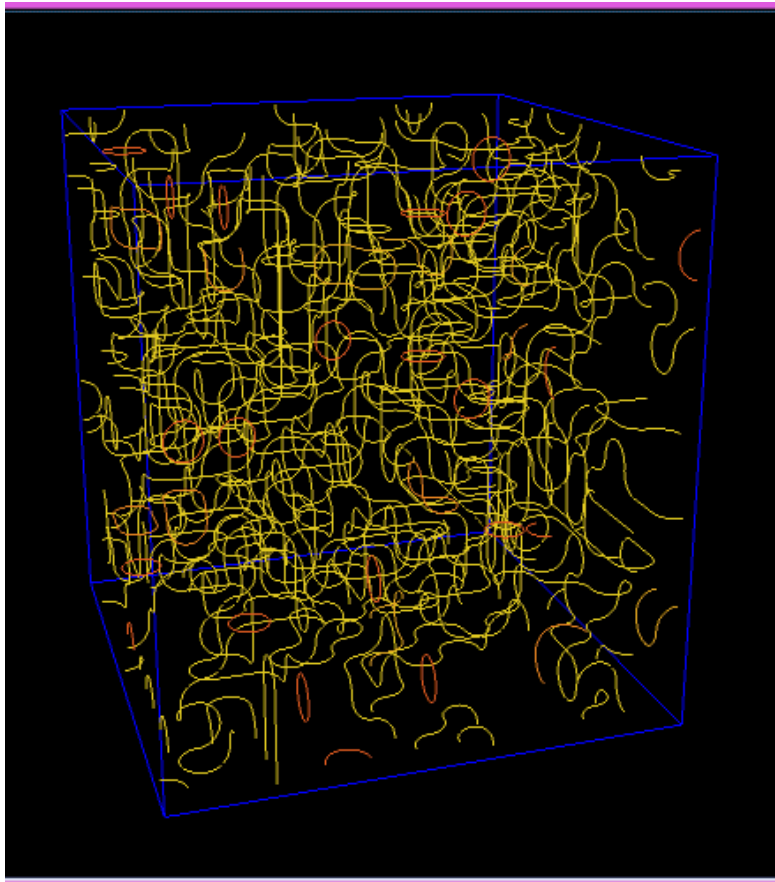


EDGE DISLOCATION:  $\mathbf{t} \perp \mathbf{B}$



# Dislocations in Solids

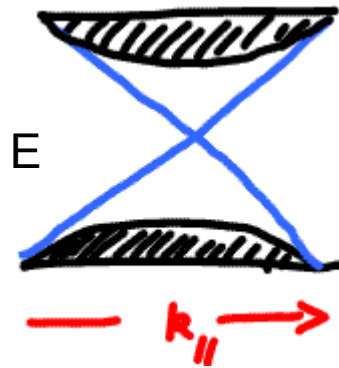
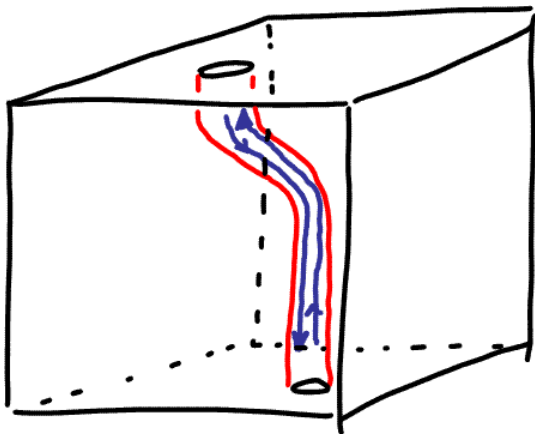
- Always present  $n_d \approx 10^{10}$  to  $10^{12} \text{m}^{-2}$
- Control mechanical properties eg. Plastic Flow
- Crystal Growth – aided by screw dislocations.



# Dislocation in a Topological Insulator

- 1D Helical Metal occurs in a dislocation  $\{\mathbf{R}(\sigma), \mathbf{B}\}$  embedded in a topological insulator  $\{\nu_0 = 0, 1; \mathbf{M}_\nu\}$  iff:

$$\mathbf{B} \cdot \mathbf{M}_\nu = \pi \pmod{2\pi}$$

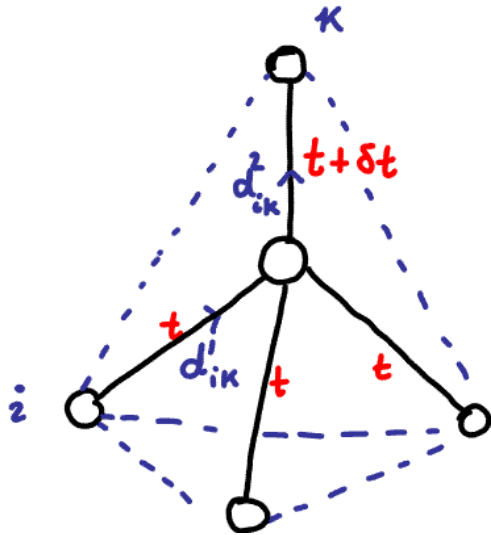


1D Modes are topologically protected:

- Cannot be gapped if Time Reversal Symmetry + bulk gap are present.
- Not localized by disorder
- Half of a regular quantum wire.

- Not all Top. Ins. have dislocation Helical modes.  
 $\nu_0 = 1; \mathbf{M}_\nu = 0$
- Modes occur for both Weak and Strong Top.Ins.

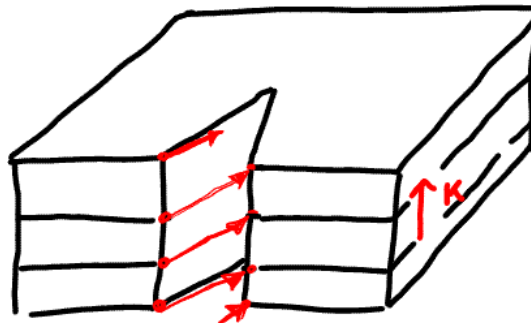
# Illustration – Diamond Lattice Top. Ins.



$$H = t \sum_{\langle ij \rangle} c_{i\sigma}^\dagger c_{j\sigma} + i \frac{\lambda_{SO}}{8a^2} \sum_{\langle\langle ik \rangle\rangle} c_{i\sigma}^\dagger (\vec{d}_{ik}^1 \times \vec{d}_{ik}^2) \cdot \vec{\sigma}_{\sigma\sigma'} c_{k\sigma'}$$

$$v_0 = 1; \mathbf{M}_v = \frac{\pi}{2} (1, 1, 1)$$

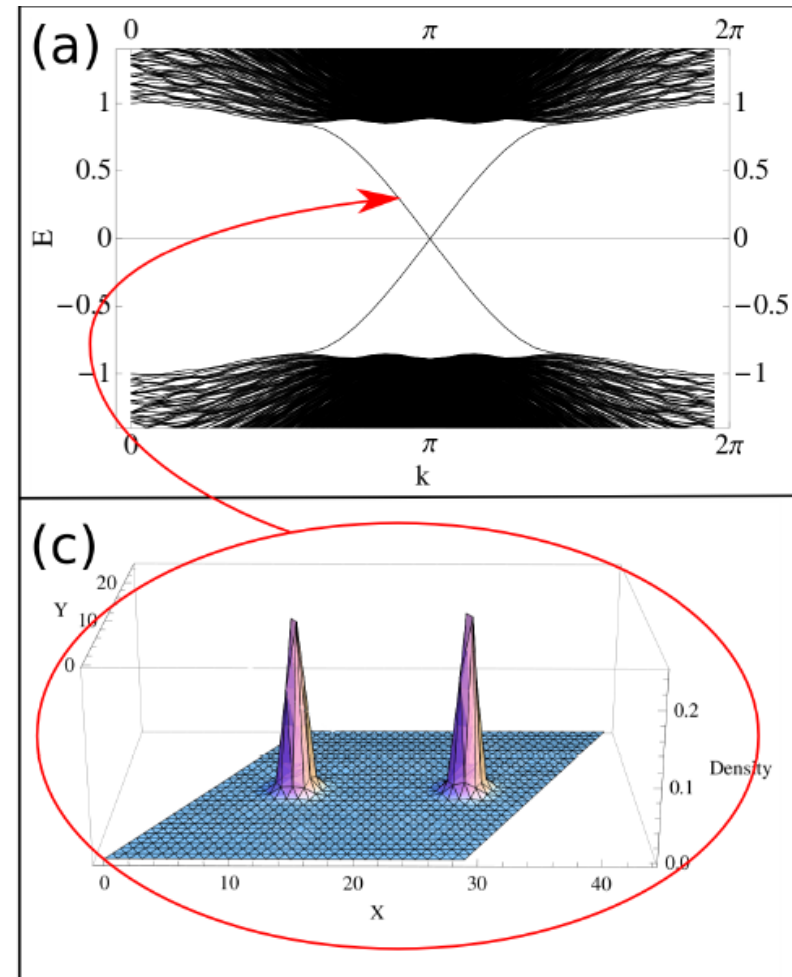
- Introduce a screw dislocation:  $\mathbf{B}=(1,1,0)$ .
  - Easily introduced in tight binding. Momentum dependent phase factor for cut bonds.



$$t \rightarrow t e^{+i\mathbf{K} \cdot \vec{B}}$$

# Results: Screw Dislocation in Diamond Lattice Top. Ins.

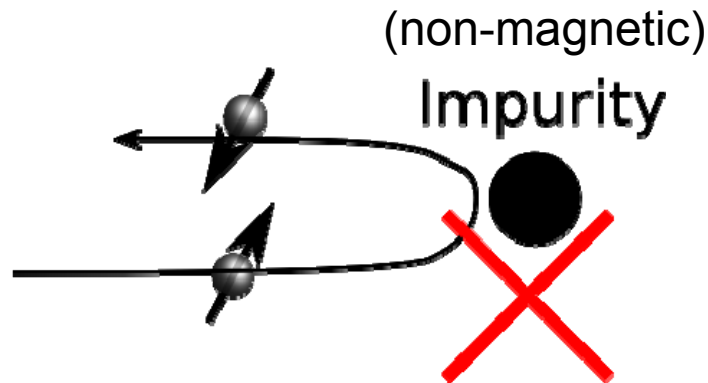
- Insert a pair of screw dislocations (36x36x18 periodic BC). Momentum along the dislocations is a good quantum number.
- Two propagating modes per dislocation. 'Helical metal'.



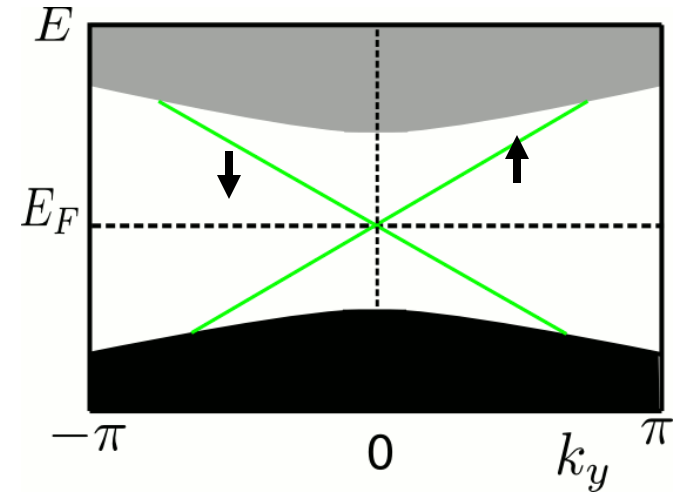
# Absence of localization

- Stable to disorder:  
(TR symmetry  $\rightarrow$  **no backscattering**)

An atomically thin one dimensional wire that does *not* localize.



Backscattering breaks  
time-reversal

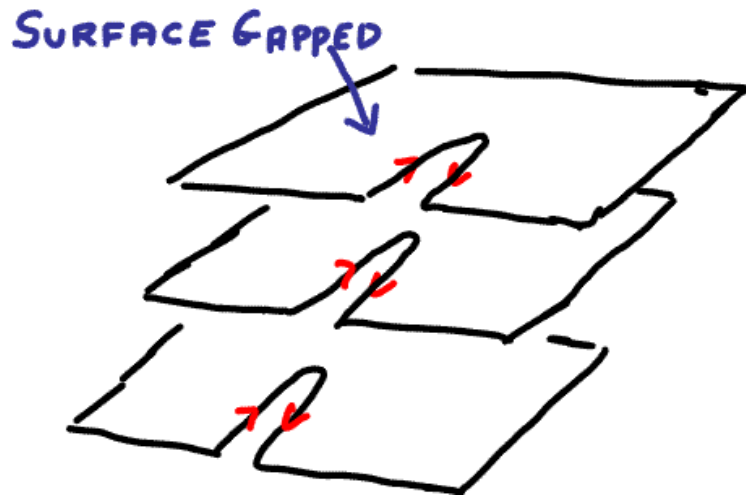


Similar to 2D quantum spin Hall edge states

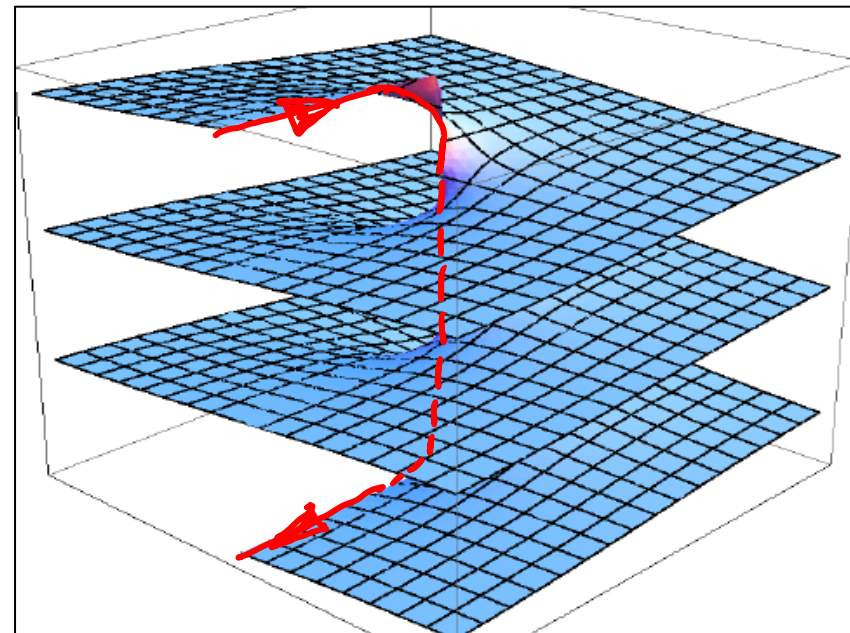
With *strong* interactions, can spontaneously break time reversal symmetry, localization

# Proof for Weak Top. Ins.

- Weak Top.Ins. Adiabatically connected to a stack of decoupled 2D Top.Ins.,
  - stacking along  $M_v$
  - Different proof for Strong TI

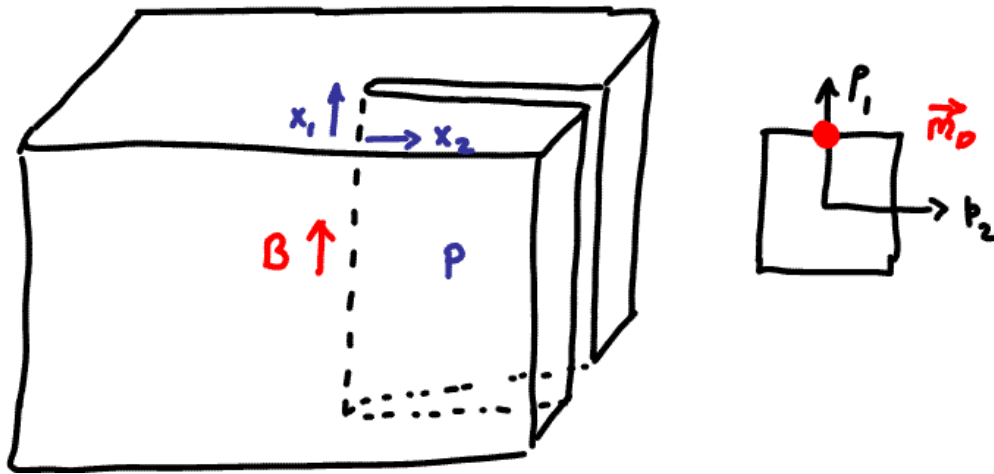


Cut Surface – only one of the helical mode pairs is shown.



Glued Surface – Dislocation must carry helical modes

# Proof For General Top. Ins. 1



- Screw dislocation – **if** surface Dirac node is at momentum  $\mathbf{m}_{\text{Dirac}} \cdot \mathbf{B} = \pi$  then  $(-1)$  phase acquired on crossing the dislocation.
- In the weak surface connection limit  $\Rightarrow$  Dirac equation that changes mass term sign.

$$H = (p_1 \sigma_1 + p_2 \sigma_2) \mu_z + m(x_2) \mu_x$$

$$m(x_2 > 0) = -m$$

$$m(x_2 < 0) = +m$$

# Proof For General Top. Ins. 2

$$H = (p_1\sigma_1 + p_2\sigma_2)\mu_z + m(x_2)\mu_x$$

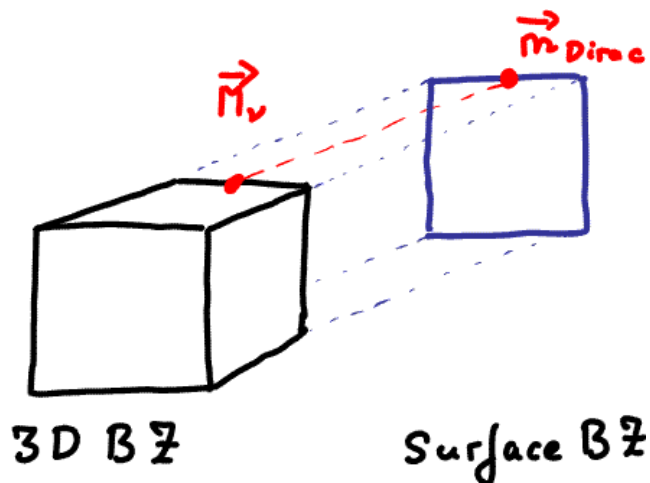
$$m(x_2 > 0) = -m$$

$$m(x_2 < 0) = +m$$

$$\psi(x_2) = \psi_0 e^{-\int_0^{x_2} |m(x')| dx'}$$

- Pair of zero modes at  $p_1=0$ .
- Propagating 1D helical modes for general  $p_1$ .

- Location of Surface Dirac Node – controlled by  $\mathbf{M}_v$



$$\mathbf{m}_{\text{Dirac}} \cdot \mathbf{B} = \pi$$

$$\Downarrow$$

$$\mathbf{M}_v \cdot \mathbf{B} = \pi \pmod{2\pi}$$

# Experimental Signatures

- Resistivity: dislocation contribution could dominate over surface conduction.

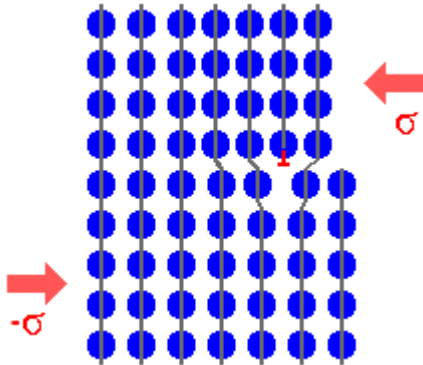


$$\rho = \frac{h}{2e^2} \frac{1}{l n_d} \approx 10^{-2} \Omega \mathbf{m} \quad \begin{array}{l} n_d \approx 10^{12} \text{ m}^{-2} \\ l \approx 1 \mu\text{m} \end{array}$$

(in current samples – impurity band conduction dominates)

# Experimental Signatures

- Dislocations can be created during plastic deformation. For the right kind of stress (connected to lattice indices  $M_v$  ) increased conductivity.



# Experimental Signatures - STM

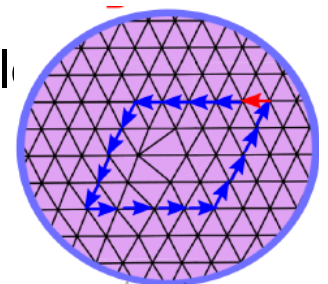
- Can determine atomic defect structure and Local Density of States (LDOS).
  - 1D modes – finite DOS. (ideally operate at Dirac point with vanishing density of states)

- Demonstration - Diamond lattice strong Top.Ins.. Edge disl

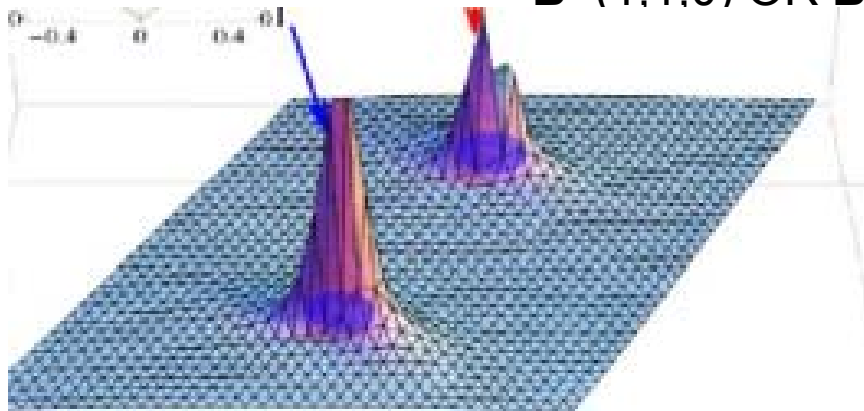
**Edge dislocation** on  $(-1,-1,1)$  Surface.

$\mathbf{B}=(1,1,0)$  OR  $\mathbf{B}=(-1,0,1)$ .

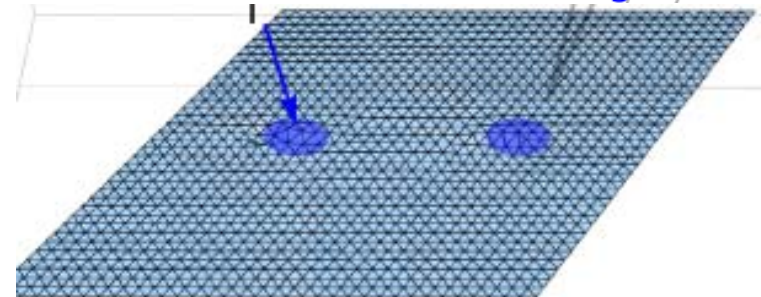
$S$  in  $[-0.1,0.1]$ .



Edge disloc.



$$\mathbf{B} \cdot \mathbf{M}_v = \pi$$



$$\mathbf{B} \cdot \mathbf{M}_v = 0$$

# Effect of Lattice Disorder

- **Very Strong Disorder** – dislocations proliferate; no meaning to  $\mathbf{M}_\nu$
  - **Moderate disorder** – dilute dislocation density. Can still characterize using gapless modes in dislocations and define  $\mathbf{M}_\nu$ . Weak insulators can be defined even *with* disorder.  
*but* Surface states localized.
- (weak insulators can be defined *even* when surface states localized)

# Conclusions

- 3D topological Band Insulator has protected helical mode in those dislocations that satisfy

$$\mathbf{B} \cdot \mathbf{M}_v = \pi \pmod{2\pi}$$

Should occur in  $\text{Bi}_{1-x}\text{Sb}_x$   $\mathbf{M}_v \propto (111)$  but not in  $\text{Bi}_2\text{Se}_3$ ,  $\text{Bi}_2\text{Te}_3$   $\mathbf{M}_v = 0$

- Indicates weak topological insulator stable to disorder if dislocations do not proliferate.
- Another example of a 'dressed' topological defect – intrinsically quantum phenomena.

Eg: Dimerized spin  $\frac{1}{2}$  chain.  
Domain walls carry spin



When defects are quantum mechanical – leads to new phases and phase transitions